NSN 5961-01-364-1982

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Diode Semiconductor Device - Page 1 of 1



View Online at https://aerobasegroup.com/nsn/5961-01-364-1982 **Inclosure Material:** Ceramic or glass or metal **Overall Length:** Between 0.150 inches and 0.170 inches **Overall Diameter:** Between 0.068 inches and 0.076 inches **Mounting Method:** Terminal **Semiconductor Material:** Silicon Voltage Rating In Volts Per Characteristic: 0.4 forward voltage, dc and 15.0 breakdown voltage, dc **Current Rating Per Characteristic:** 100.00 nanoamperes forward current, average peak and 20.00 milliamperes service voltage preset **Power Rating Per Characteristic:** 250.0 milliwatts small-signal input power, common-emitter outside diameter **Capacitance Rating In Picofarads:** 1.2 **Maximum Operating Tempurature Per Measurement Point:** 200.0 degrees celsius ambient air **Terminal Type And Quantity:** 2 uninsulated wire lead Shelf Life: N/a **Unit Of Measure: Demilitarization:** No